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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	100MHz
Primary Attributes	ProASIC®3 FPGA, 500K Gates, 11520 D-Flip-Flops
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	288-TFBGA, CSPBGA
Supplier Device Package	288-CSP (11x11)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f500m3g-1cs288

VCCxxxxIOBx Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCxxxxIOBx ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- By default, during programming I/Os become tristated and weakly pulled up to VCCxxxxIOBx. You can modify the I/O states during programming in FlashPro. For more details, refer to "Specifying I/O States During Programming" on page 1-3.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

The Microsemi SoC Products Group recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLx exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 on page 2-6 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation

Theta-JA

Junction-to-ambient thermal resistance (θ_{JA}) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It should be used with caution but is useful for comparing the thermal performance of one package to another.

A sample calculation showing the maximum power dissipation allowed for the A2F200-FG484 package under forced convection of 1.0 m/s and 75°C ambient temperature is as follows:

$$\text{Maximum Power Allowed} = \frac{T_{J(MAX)} - T_{A(MAX)}}{\theta_{JA}}$$

EQ 4

where

θ_{JA} = 19.00°C/W (taken from Table 2-6 on page 2-7).

T_A = 75.00°C

$$\text{Maximum Power Allowed} = \frac{100.00°C - 75.00°C}{19.00°C/W} = 1.3\ W$$

EQ 5

The power consumption of a device can be calculated using the Microsemi SoC Products Group power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package. If the power consumption is higher than the device's maximum allowable power dissipation, a heat sink can be attached on top of the case, or the airflow inside the system must be increased.

Theta-JB

Junction-to-board thermal resistance (θ_{JB}) measures the ability of the package to dissipate heat from the surface of the chip to the PCB. As defined by the JEDEC (JESD-51) standard, the thermal resistance from junction to board uses an isothermal ring cold plate zone concept. The ring cold plate is simply a means to generate an isothermal boundary condition at the perimeter. The cold plate is mounted on a JEDEC standard board with a minimum distance of 5.0 mm away from the package edge.

Theta-JC

Junction-to-case thermal resistance (θ_{JC}) measures the ability of a device to dissipate heat from the surface of the chip to the top or bottom surface of the package. It is applicable for packages used with external heat sinks. Constant temperature is applied to the surface in consideration and acts as a boundary condition. This only applies to situations where all or nearly all of the heat is dissipated through the surface in consideration.

Calculation for Heat Sink

For example, in a design implemented in an A2F200-FG484 package with 2.5 m/s airflow, the power consumption value using the power calculator is 3.00 W. The user-dependent T_a and T_j are given as follows:

T_J = 100.00°C

T_A = 70.00°C

From the datasheet:

θ_{JA} = 17.00°C/W

θ_{JC} = 8.28°C/W

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100°C - 70°C}{17.00\ W} = 1.76\ W$$

EQ 6

The 1.76 W power is less than the required 3.00 W. The design therefore requires a heat sink, or the airflow where the device is mounted should be increased. The design's total junction-to-air thermal resistance requirement can be estimated by EQ 7:

$$\theta_{JA(total)} = \frac{T_J - T_A}{P} = \frac{100°C - 70°C}{3.00\ W} = 10.00°C/W$$

EQ 7

Determining the heat sink's thermal performance proceeds as follows:

$$\theta_{JA(TOTAL)} = \theta_{JC} + \theta_{CS} + \theta_{SA}$$

EQ 8

where

θ_{JA} = 0.37°C/W

= Thermal resistance of the interface material between the case and the heat sink, usually provided by the thermal interface manufacturer

θ_{SA} = Thermal resistance of the heat sink in °C/W

$$\theta_{SA} = \theta_{JA(TOTAL)} - \theta_{JC} - \theta_{CS}$$

EQ 9

$$\theta_{SA} = 13.33°C/W - 8.28°C/W - 0.37°C/W = 5.01°C/W$$

A heat sink with a thermal resistance of 5.01°C/W or better should be used. Thermal resistance of heat sinks is a function of airflow. The heat sink performance can be significantly improved with increased airflow.

Carefully estimating thermal resistance is important in the long-term reliability of an FPGA. Design engineers should always correlate the power consumption of the device with the maximum allowable power dissipation of the package selected for that device.

Note: The junction-to-air and junction-to-board thermal resistances are based on JEDEC standard (JESD-51) and assumptions made in building the model. It may not be realized in actual application and therefore should be used with a degree of caution. Junction-to-case thermal resistance assumes that all power is dissipated through the case.

Temperature and Voltage Derating Factors

Table 2-7 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 85°C, worst-case VCC = 1.425 V)**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	**0°C**	**25°C**	**70°C**	**85°C**	**100°C**
1.425	0.86	0.91	0.93	0.98	1.00	1.02
1.500	0.81	0.86	0.88	0.93	0.95	0.96
1.575	0.78	0.83	0.85	0.90	0.91	0.93

Standby Mode and Time Keeping Mode

P_{NET} = 0 W

I/O Input Buffer Dynamic Contribution—P_{INPUTS}

SoC Mode

$P_{INPUTS} = N_{INPUTS} * (\alpha_2 / 2) * P_{AC9} * F_{CLK}$

Where:

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

P_{INPUTS} = 0 W

I/O Output Buffer Dynamic Contribution—$P_{OUTPUTS}$

SoC Mode

$P_{OUTPUTS} = N_{OUTPUTS} * (\alpha_2 / 2) * \beta_1 * P_{AC10} * F_{CLK}$

Where:

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-17 on page 2-18.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-18 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$P_{OUTPUTS}$ = 0 W

FPGA Fabric SRAM Dynamic Contribution—P_{MEMORY}

SoC Mode

$P_{MEMORY} = (N_{BLOCKS} * P_{AC11} * \beta_2 * F_{READ\text{-}CLOCK}) + (N_{BLOCKS} * P_{AC12} * \beta_3 * F_{WRITE\text{-}CLOCK})$

Where:

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ\text{-}CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations—guidelines are provided in Table 2-18 on page 2-18.

β_3 the RAM enable rate for write operations—guidelines are provided in Table 2-18 on page 2-18.

$F_{WRITE\text{-}CLOCK}$ is the memory write clock frequency.

Standby Mode and Time Keeping Mode

P_{MEMORY} = 0 W

PLL/CCC Dynamic Contribution—P_{PLL}

SoC Mode

$P_{PLL} = P_{AC13} * F_{CLKOUT}$

F_{CLKIN} is the input clock frequency.

F_{CLKOUT} is the output clock frequency.[1]

Standby Mode and Time Keeping Mode

1. *The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula output clock by adding its corresponding contribution ($P_{AC14} * F_{CLKOUT}$ product) to the total PLL contribution.*

Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings –1 Speed Grade, Worst Commercial-Case Conditions: T_J = 85°C, Worst Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx (per standard) Applicable to FPGA I/O Banks, Assigned to EMC I/O Pins

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
2.5 V LVCMOS	12 mA	High	35	–	0.50	2.73	0.03	1.03	0.32	2.88	2.69	2.62	2.70	4.60	4.41	ns
1.8 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
1.5 V LVCMOS	12 mA	High	35	–	0.50	3.24	0.03	1.12	0.32	3.30	2.79	3.10	3.27	5.02	4.50	ns
3.3 V PCI	Per PCI spec	High	10	25[1]	0.50	2.11	0.03	0.68	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
3.3 V PCI-X	Per PCI-X spec	High	10	25[1]	0.50	2.11	0.03	0.64	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
LVDS	24 mA	High	–	–	0.50	1.53	0.03	1.55	–	–	–	–	–	–	–	ns
LVPECL	24 mA	High	–	–	0.50	1.46	0.03	1.46	–	–	–	–	–	–	–	ns

Notes:

1. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-10 on page 2-39 for connectivity. This resistor is not required during normal operation.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings –1 Speed Grade, Worst Commercial-Case Conditions: T_J = 85°C, Worst Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx (per standard) Applicable to MSS I/O Banks

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	High	10	–	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns
2.5 V LVCMOS	8 mA	High	10	–	0.18	1.96	0.07	0.99	1.16	0.18	2.00	1.82	1.82	1.93	ns
1.8 V LVCMOS	4 mA	High	10	–	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns
1.5 V LVCMOS	2 mA	High	10	–	0.18	2.70	0.07	1.07	1.55	0.18	2.75	2.67	1.87	1.85	ns

Notes:

1. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-10 on page 2-39 for connectivity. This resistor is not required during normal operation.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Detailed I/O DC Characteristics

***Table 2-26* • Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	V_{IN} = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	V_{IN} = 0, f = 1.0 MHz		8	pF

***Table 2-27* • I/O Output Buffer Maximum Resistances[1]**
Applicable to FPGA I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website (also generated by the SoC Products Group Libero SoC toolset).*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$

Timing Characteristics

Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	7.20	0.04	0.97	0.39	7.34	6.18	2.52	2.46	9.39	8.23	ns
	–1	0.50	6.00	0.03	0.81	0.32	6.11	5.15	2.10	2.05	7.83	6.86	ns
8 mA	Std.	0.60	4.64	0.04	0.97	0.39	4.73	3.84	2.85	3.02	6.79	5.90	ns
	–1	0.50	3.87	0.03	0.81	0.32	3.94	3.20	2.37	2.52	5.65	4.91	ns
12 mA	Std.	0.60	3.37	0.04	0.97	0.39	3.43	2.67	3.07	3.39	5.49	4.73	ns
	–1	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
16 mA	Std.	0.60	3.18	0.04	0.97	0.39	3.24	2.43	3.11	3.48	5.30	4.49	ns
	–1	0.50	2.65	0.03	0.81	0.32	2.70	2.03	2.59	2.90	4.42	3.74	ns
24 mA	Std.	0.60	2.93	0.04	0.97	0.39	2.99	2.03	3.17	3.83	5.05	4.09	ns
	–1	0.50	2.45	0.03	0.81	0.32	2.49	1.69	2.64	3.19	4.21	3.41	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	9.75	0.04	0.97	0.39	9.93	8.22	2.52	2.31	11.99	10.28	ns
	–1	0.50	8.12	0.03	0.81	0.32	8.27	6.85	2.10	1.93	9.99	8.57	ns
8 mA	Std.	0.60	6.96	0.04	0.97	0.39	7.09	5.85	2.84	2.87	9.15	7.91	ns
	–1	0.50	5.80	0.03	0.81	0.32	5.91	4.88	2.37	2.39	7.62	6.59	ns
12 mA	Std.	0.60	5.35	0.04	0.97	0.39	5.45	4.58	3.06	3.23	7.51	6.64	ns
	–1	0.50	4.46	0.03	0.81	0.32	4.54	3.82	2.55	2.69	6.26	5.53	ns
16 mA	Std.	0.60	5.01	0.04	0.97	0.39	5.10	4.30	3.11	3.32	7.16	6.36	ns
	–1	0.50	4.17	0.03	0.81	0.32	4.25	3.58	2.59	2.77	5.97	5.30	ns
24 mA	Std.	0.60	4.67	0.04	0.97	0.39	4.75	4.28	3.16	3.66	6.81	6.34	ns
	–1	0.50	3.89	0.03	0.81	0.32	3.96	3.57	2.64	3.05	5.68	5.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-40 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
8 mA	Std.	0.22	2.31	0.09	0.94	1.30	0.22	2.35	1.86	2.20	2.45	ns
	–1	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. SoC Products Group LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using SoC Products Group LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-12. The input and output buffer delays are available in the LVDS section in Table 2-65.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case commercial operating conditions, at the farthest receiver: R_S = 60 Ω and R_T = 70 Ω, given Z_0 = 50 Ω (2") and Z_{stub} = 50 Ω (~1.5").

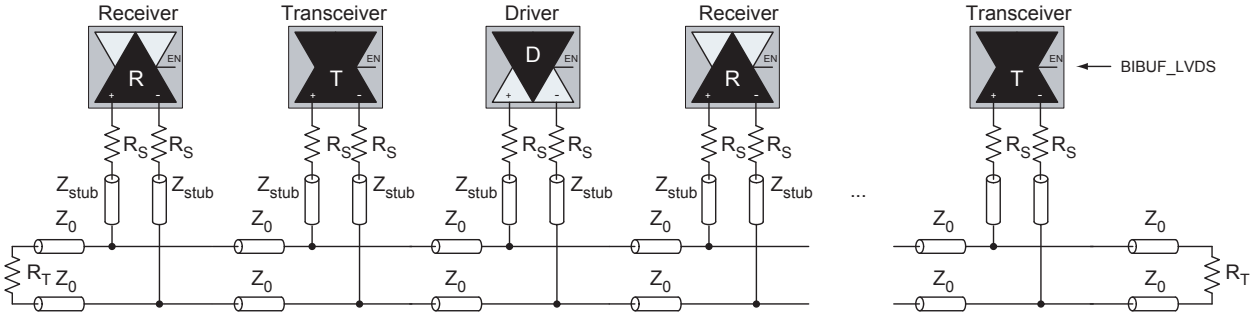

Figure 2-12 • **B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers**

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-13. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

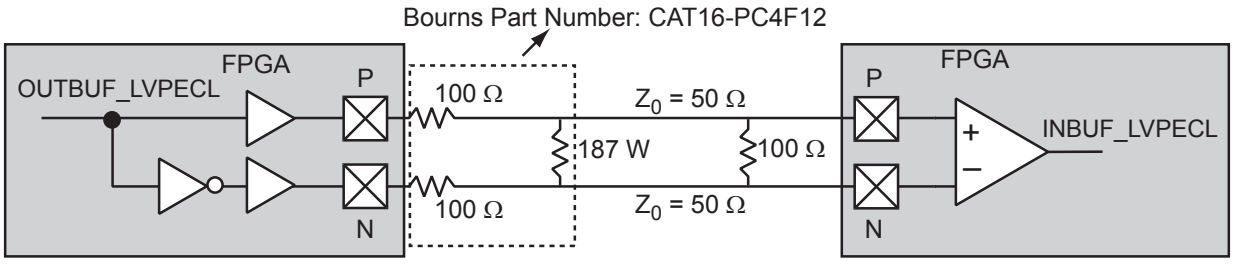

Figure 2-13 • **LVPECL Circuit Diagram and Board-Level Implementation**

FPGA Fabric SRAM and FIFO Characteristics

FPGA Fabric SRAM

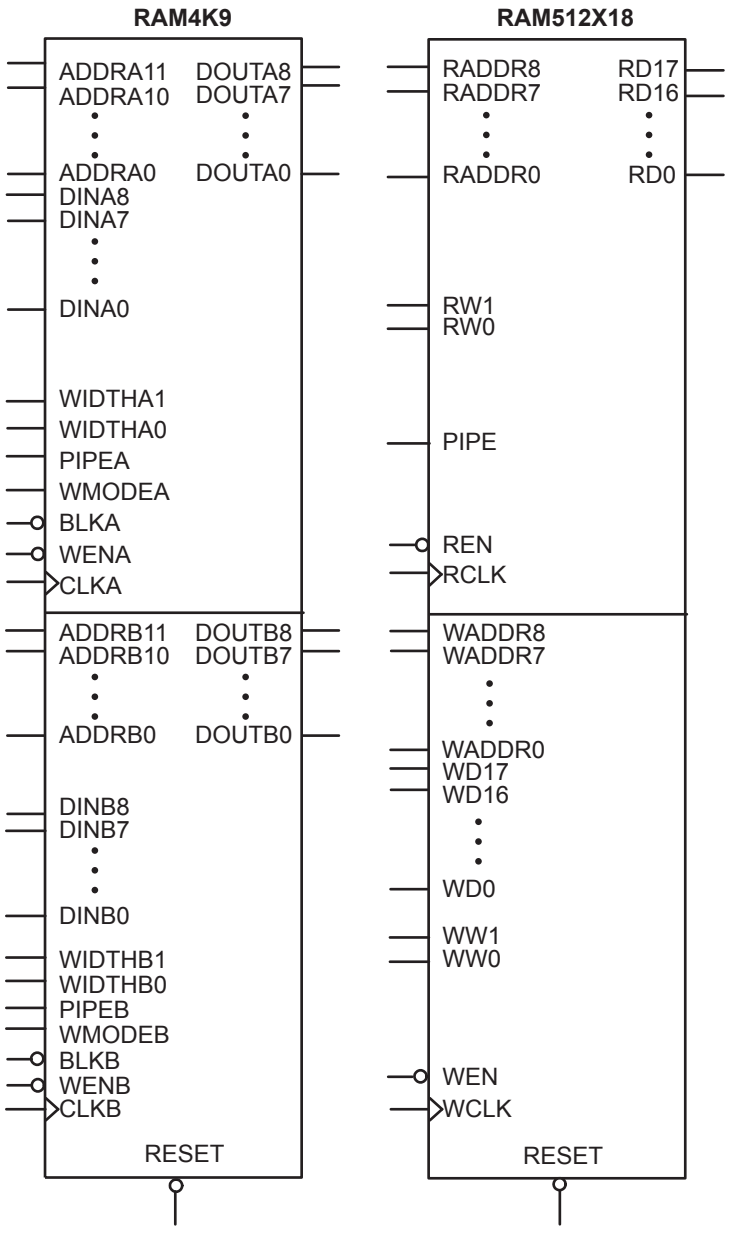

Figure 2-29 • **RAM Models**

Timing Characteristics

Table 2-87 • RAM4K9
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.30	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.12	ns
t_{BKS}	BLK setup time	0.24	0.28	ns
t_{BKH}	BLK hold time	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.19	0.22	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.81	2.18	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.39	2.87	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.91	1.09	ns
t_{C2CWWH}[1]	Address collision clk-to-clk delay for reliable write after write on same address—applicable to rising edge	0.23	0.26	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—applicable to opening edge	0.34	0.38	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address— applicable to opening edge	0.37	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.94	1.12	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.94	1.12	ns
$t_{REMRSTB}$	RESET removal	0.29	0.35	ns
$t_{RECRSTB}$	RESET recovery	1.52	1.83	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.22	0.22	ns
t_{CYC}	Clock cycle time	3.28	3.28	ns
F_{MAX}	Maximum clock frequency	305	305	MHz

Notes:

1. *For more information, refer to the Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs application note.*
2. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

User-Defined Supply Pins

Name	Type	Polarity/ Bus Size	Description
VAREF0	Input	1	Analog reference voltage for first ADC. The SmartFusion cSoC can be configured to generate a 2.56 V internal reference that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREFOUT pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF0 is internally generated, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 µF and 22 µF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF0 signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF0 to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. See the Analog-to-Digital Converter (ADC) section in the *SmartFusion Programmable Analog User's Guide* for more information. The SoC Products Group recommends customers use 10 µF as the value of the bypass capacitor. Designers choosing to use an external VAREF0 need to ensure that a stable and clean VAREF0 source is supplied to the VAREF0 pin before initiating conversions by the ADC. To use the internal voltage reference, the VAREFOUT pin must be connected to the appropriate ADC VAREFx input on the PCB. For example, VAREFOUT can be connected to VAREF0 only, if ADC0 alone is used. VAREFOUT can be connected to VAREF1 only, if ADC1 alone is used. VAREFOUT can be connected to VAREF2 only, if ADC2 alone is used. VAREFOUT can be connected to VAREF0, VAREF1 and VAREF2 together, if ADC0, ADC1, and ADC2 all are used.
VAREF1	Input	1	Analog reference voltage for second ADC See "VAREF0" above for more information.
VAREF2	Input	1	Analog reference voltage for third ADC See "VAREF0" above for more.
VAREFOUT	Out	1	Internal 2.56 V voltage reference output. Can be used to provide the two ADCs with a unique voltage reference externally by connecting VAREFOUT to both VAREF0 and VAREF1. To use the internal voltage reference, you must connect the VAREFOUT pin to the appropriate ADC VAREFx input—either the VAREF0 or VAREF1 pin—on the PCB.

TQ144	
Pin Number	**A2F060 Function**
1	VCCPLL0
2	VCOMPLA0
3	GNDQ
4	GFA2/IO42PDB5V0
5	GFB2/IO42NDB5V0
6	GFC2/IO41PDB5V0
7	IO41NDB5V0
8	VCC
9	GND
10	VCCFPGAIOB5
11	IO38PDB5V0
12	IO38NDB5V0
13	IO36PDB5V0
14	IO36NDB5V0
15	GND
16	GNDRCOSC
17	VCCRCOSC
18	MSS_RESET_N
19	GPIO_0/IO33RSB4V0
20	GPIO_1/IO32RSB4V0
21	GPIO_2/IO31RSB4V0
22	GPIO_3/IO30RSB4V0
23	GPIO_4/IO29RSB4V0
24	GND
25	VCCMSSIOB4
26	VCC
27	GPIO_5/IO28RSB4V0
28	GPIO_6/IO27RSB4V0
29	GPIO_7/IO26RSB4V0
30	GPIO_8/IO25RSB4V0
31	VCCESRAM
32	GNDSDD0
33	VCC33SDD0
34	VCC15A
35	PCAP
36	NCAP

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
F12	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO14NDB0V0
F13	GND	GND	GND
F14	GCB1/IO19PPB0V0	GCC1/IO26PPB1V0	GCC1/IO35PPB1V0
F15	GNDQ	GNDQ	GNDQ
F16	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
F17	GCB0/IO19NPB0V0	IO24NDB1V0	IO33NDB1V0
F19	IO23NDB1V0	GDB1/IO30PDB1V0	GDB1/IO39PDB1V0
F21	GCA2/IO21PDB1V0	GDB0/IO30NDB1V0	GDB0/IO39NDB1V0
G1	IO41NDB5V0	IO67NDB5V0	IO84NDB5V0
G3	GFC2/IO41PDB5V0	GFC2/IO67PDB5V0	GFC2/IO84PDB5V0
G5	NC	GFB1/IO65PDB5V0	GFB1/IO82PDB5V0
G6	EMC_DB[10]/IO43NDB5V0	EMC_DB[10]/IO69NDB5V0	EMC_DB[10]/IO86NDB5V0
G9	NC	GFC0/IO66NPB5V0	GFC0/IO83NPB5V0
G13	GCA0/IO20NPB0V0	GCC0/IO26NPB1V0	GCC0/IO35NPB1V0
G16	NC	GDA0/IO31NDB1V0	GDA0/IO40NDB1V0
G17	IO22NPB1V0	GDC1/IO29PDB1V0	GDC1/IO38PDB1V0
G19	GCC2/IO23PDB1V0	GDC0/IO29NDB1V0	GDC0/IO38NDB1V0
G21	GND	GND	GND
H1	EMC_DB[9]/IO40PPB5V0	EMC_DB[9]/GEC1/IO63PPB5V0	EMC_DB[9]/GEC1/IO80PPB5V0
H3	GND	GND	GND
H5	NC	GFB0/IO65NDB5V0	GFB0/IO82NDB5V0
H6	EMC_DB[7]/IO39PDB5V0	EMC_DB[7]/GEB1/IO62PDB5V0	EMC_DB[7]/GEB1/IO79PDB5V0
H8	GND	GND	GND
H9	VCC	VCC	VCC
H10	GND	GND	GND
H11	VCC	VCC	VCC
H12	GND	GND	GND
H13	VCC	VCC	VCC
H14	GND	GND	GND
H16	NC	GDA1/IO31PDB1V0	GDA1/IO40PDB1V0
H17	NC	GDC2/IO32PPB1V0	GDC2/IO41PPB1V0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
K17	GNDLPXTAL	GNDLPXTAL	GNDLPXTAL
K19	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL
K21	MAINXIN	MAINXIN	MAINXIN
L1	GNDRCOSC	GNDRCOSC	GNDRCOSC
L3	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
L5	EMC_DB[2]/IO37NPB5V0	EMC_DB[2]/IO60NPB5V0	EMC_DB[2]/IO77NPB5V0
L6	NC	GNDQ	GNDQ
L8	VCC	VCC	VCC
L9	GND	GND	GND
L10	VCC	VCC	VCC
L12	VCC	VCC	VCC
L13	GND	GND	GND
L14	VCC	VCC	VCC
L16	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL
L17	VDDBAT	VDDBAT	VDDBAT
L19	LPXIN	LPXIN	LPXIN
L21	MAINXOUT	MAINXOUT	MAINXOUT
M1	VCCRCOSC	VCCRCOSC	VCCRCOSC
M3	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N
M5	GPIO_5/IO28RSB4V0	GPIO_5/IO42RSB4V0	GPIO_5/IO51RSB4V0
M6	GND	GND	GND
M8	GND	GND	GND
M9	VCC	VCC	VCC
M10	GND	GND	GND
M11	VCC	VCC	VCC
M12	GND	GND	GND
M13	VCC	VCC	VCC
M14	GND	GND	GND
M16	TMS	TMS	TMS
M17	VJTAG	VJTAG	VJTAG
M19	TDO	TDO	TDO

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
M21	TRSTB	TRSTB	TRSTB
N1	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
N3	GND	GND	GND
N5	GPIO_4/IO29RSB4V0	GPIO_4/IO43RSB4V0	GPIO_4/IO52RSB4V0
N6	GPIO_8/IO25RSB4V0	GPIO_8/IO39RSB4V0	GPIO_8/IO48RSB4V0
N7	GPIO_9/IO24RSB4V0	GPIO_9/IO38RSB4V0	GPIO_9/IO47RSB4V0
N8	VCC	VCC	VCC
N9	GND	GND	GND
N10	VCC	VCC	VCC
N11	GND	GND	GND
N12	VCC	VCC	VCC
N13	GND	GND	GND
N14	VCC	VCC	VCC
N15	GND	GND	GND
N16	TCK	TCK	TCK
N17	TDI	TDI	TDI
N19	GNDENVM	GNDENVM	GNDENVM
N21	VCCENVM	VCCENVM	VCCENVM
P1	GPIO_0/IO33RSB4V0	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0
P3	GPIO_7/IO26RSB4V0	GPIO_7/IO40RSB4V0	GPIO_7/IO49RSB4V0
P5	GPIO_6/IO27RSB4V0	GPIO_6/IO41RSB4V0	GPIO_6/IO50RSB4V0
P6	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
P8	GND	GND	GND
P9	VCC	VCC	VCC
P10	GND	GND	GND
P11	VCC	VCC	VCC
P12	GND	GND	GND
P13	VCC	VCC	VCC
P14	GND	GND	GND
P16	JTAGSEL	JTAGSEL	JTAGSEL
P17	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

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Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
B16	GNDQ	GNDQ	GNDQ
C1	EMC_DB[14]/IO45NDB5V0	EMC_DB[14]/GAB2/IO71NDB5V0	EMC_DB[14]/GAB2/IO88NDB5V0
C2	VCCPLL0	VCCPLL	VCCPLL0
C3	EMC_BYTEN[0]/IO02NDB0V0	EMC_BYTEN[0]/GAC0/IO02NDB0V0	EMC_BYTEN[0]/GAC0/IO07NDB0V0
C4	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
C5	EMC_CS0_N/IO01NDB0V0	EMC_CS0_N/GAB0/IO01NDB0V0	EMC_CS0_N/GAB0/IO05NDB0V0
C6	EMC_CS1_N/IO01PDB0V0	EMC_CS1_N/GAB1/IO01PDB0V0	EMC_CS1_N/GAB1/IO05PDB0V0
C7	GND	GND	GND
C8	EMC_AB[8]/IO08NDB0V0	EMC_AB[8]/IO08NDB0V0	EMC_AB[8]/IO13NDB0V0
C9	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO11PDB0V0
C10	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
C11	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO17PDB0V0
C12	EMC_AB[19]/IO13PDB0V0	EMC_AB[19]/IO13PDB0V0	EMC_AB[19]/IO18PDB0V0
C13	GND	GND	GND
C14	GCC0/IO18NPB0V0	GBA2/IO20PPB1V0	GBA2/IO27PPB1V0
C15	GCB0/IO19NDB0V0	GCA2/IO23PDB1V0	GCA2/IO28PDB1V0 *
C16	GCB1/IO19PDB0V0	IO23NDB1V0	IO28NDB1V0
D1	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
D2	VCOMPLA0	VCOMPLA	VCOMPLA0
D3	GND	GND	GND
D4	GNDQ	GNDQ	GNDQ
D5	EMC_CLK/IO00NDB0V0	EMC_CLK/GAA0/IO00NDB0V0	EMC_CLK/GAA0/IO02NDB0V0
D6	EMC_RW_N/IO00PDB0V0	EMC_RW_N/GAA1/IO00PDB0V0	EMC_RW_N/GAA1/IO02PDB0V0
D7	EMC_AB[6]/IO07NDB0V0	EMC_AB[6]/IO07NDB0V0	EMC_AB[6]/IO12NDB0V0
D8	EMC_AB[7]/IO07PDB0V0	EMC_AB[7]/IO07PDB0V0	EMC_AB[7]/IO12PDB0V0
D9	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO11NDB0V0
D10	EMC_AB[22]/IO15NDB0V0	EMC_AB[22]/IO15NDB0V0	EMC_AB[22]/IO19NDB0V0
D11	EMC_AB[23]/IO15PDB0V0	EMC_AB[23]/IO15PDB0V0	EMC_AB[23]/IO19PDB0V0
D12	GNDQ	GNDQ	GNDQ
D13	GCC1/IO18PPB0V0	GBB2/IO20NPB1V0	GBB2/IO27NPB1V0
D14	GCA0/IO20NDB0V0	GCB2/IO24PDB1V0	GCB2/IO33PDB1V0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
D15	GCA1/IO20PDB0V0	IO24NDB1V0	IO33NDB1V0
D16	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E1	EMC_DB[13]/IO44PDB5V0	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
E2	EMC_DB[12]/IO44NDB5V0	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
E3	GFA2/IO42PDB5V0	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
E4	EMC_DB[10]/IO43NPB5V0	EMC_DB[10]/IO69NPB5V0	EMC_DB[10]/IO86NPB5V0
E5	GNDQ	GNDQ	GNDQ
E6	GND	GND	GND
E7	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E8	GND	GND	GND
E9	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E10	GND	GND	GND
E11	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E12	GCB2/IO22PDB1V0	GCA1/IO28PDB1V0	GCA1/IO36PDB1V0 *
E13	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E14	GCA2/IO21PDB1V0	GCB1/IO27PDB1V0	GCB1/IO34PDB1V0
E15	GCC2/IO23PDB1V0	GDC1/IO29PDB1V0	GDC1/IO38PDB1V0
E16	IO23NDB1V0	GDC0/IO29NDB1V0	GDC0/IO38NDB1V0
F1	EMC_DB[9]/IO40PDB5V0	EMC_DB[9]/GEC1/IO63PDB5V0	EMC_DB[9]/GEC1/IO80PDB5V0
F2	GND	GND	GND
F3	GFB2/IO42NDB5V0	GFB2/IO68NDB5V0	GFB2/IO85NDB5V0
F4	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F5	EMC_DB[11]/IO43PPB5V0	EMC_DB[11]/IO69PPB5V0	EMC_DB[11]/IO86PPB5V0
F6	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F7	GND	GND	GND
F8	VCC	VCC	VCC
F9	GND	GND	GND
F10	VCC	VCC	VCC
F11	GND	GND	GND
F12	IO22NDB1V0	GCA0/IO28NDB1V0	GCA0/IO36NDB1V0 *
F13	NC	GNDQ	GNDQ

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
T9	VAREF0	VAREF1	VAREF1
T10	ABPS0	ABPS6	ABPS6
T11	NC	ABPS5	ABPS5
T12	NC	SDD1	SDD1
T13	GNDVAREF	GNDVAREF	GNDVAREF
T14	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL
T15	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL
T16	PU_N	PU_N	PU_N

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
L9	VCC	VCC
L10	GND	GND
L11	VCC	VCC
L12	GND	GND
L13	VCC	VCC
L14	GND	GND
L15	VCC	VCC
L16	GND	GND
L17	GNDQ	GNDQ
L18	GDA2/IO33NDB1V0	GDA2/IO42NDB1V0
L19	VCCFPGAIOB1	VCCFPGAIOB1
L20	GDB1/IO30PDB1V0	GDB1/IO39PDB1V0
L21	GDB0/IO30NDB1V0	GDB0/IO39NDB1V0
L22	GDC2/IO32PDB1V0	GDC2/IO41PDB1V0
M1	NC	IO71PDB5V0
M2	NC	IO71NDB5V0
M3	VCCFPGAIOB5	VCCFPGAIOB5
M4	NC	IO72NPB5V0
M5	GNDQ	GNDQ
M6	NC	IO68PDB5V0
M7	GND	GND
M8	VCC	VCC
M9	GND	GND
M10	VCC	VCC
M11	GND	GND
M12	VCC	VCC
M13	GND	GND
M14	VCC	VCC
M15	GND	GND
M16	VCCFPGAIOB1	VCCFPGAIOB1
M17	NC	NC
M18	GDB2/IO33PDB1V0	GDB2/IO42PDB1V0
M19	VJTAG	VJTAG
M20	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*